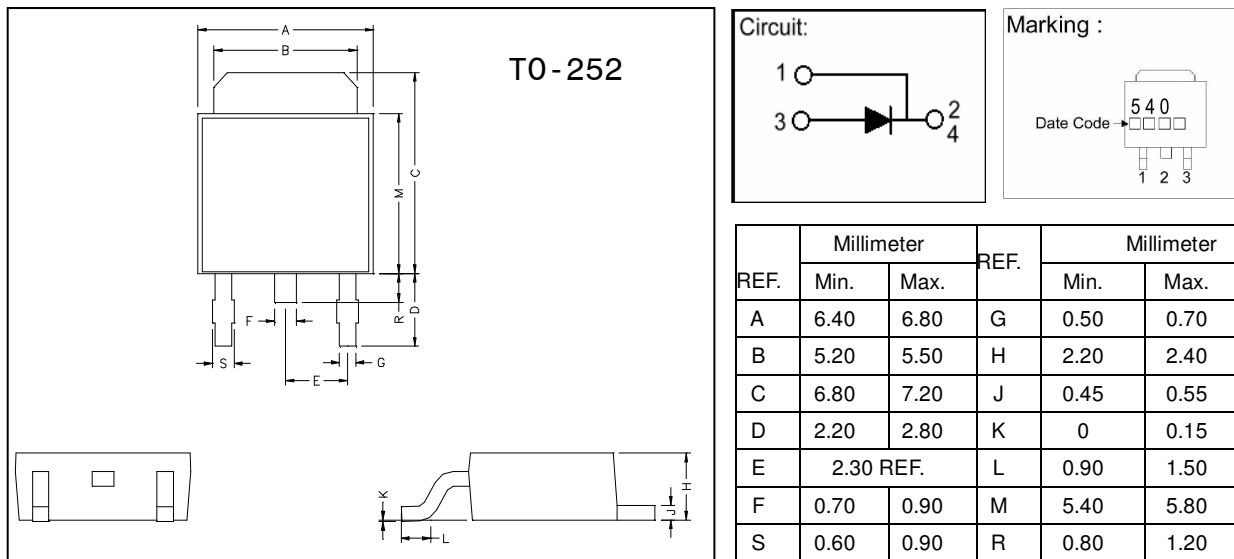


GBL540

Description

The GBL540 is designed for Low Voltage, High Frequency Inverter, Free Wheeling, and Polarity Protection Application.

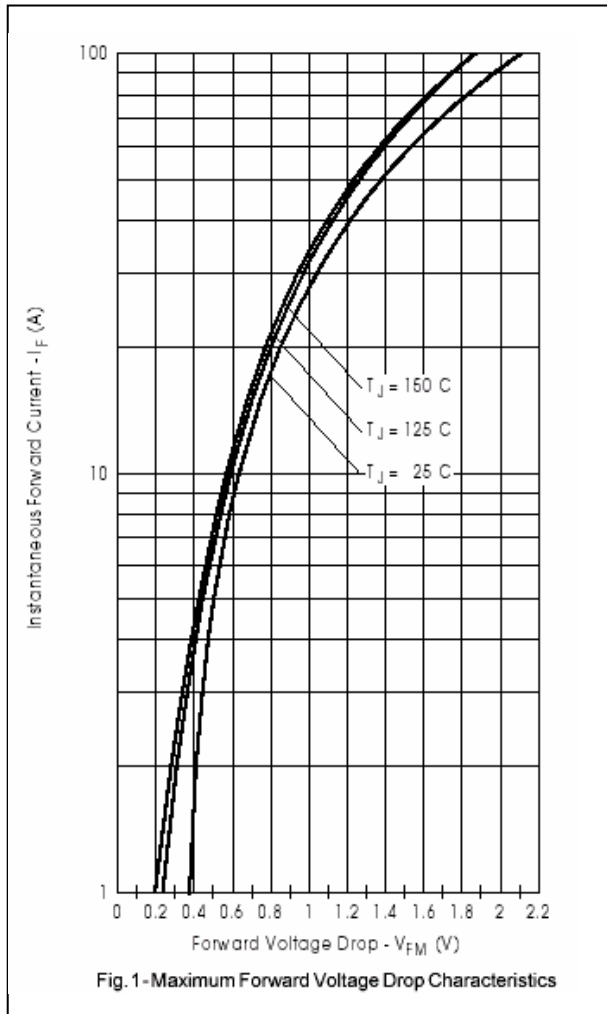
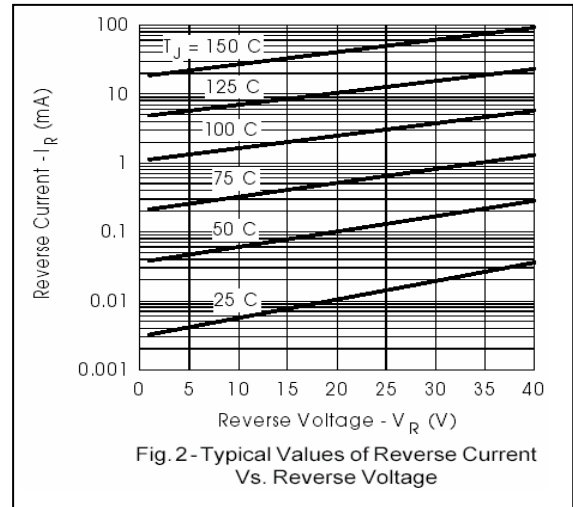
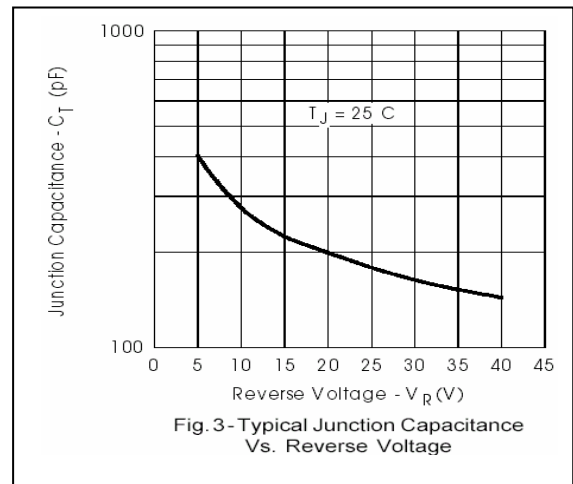
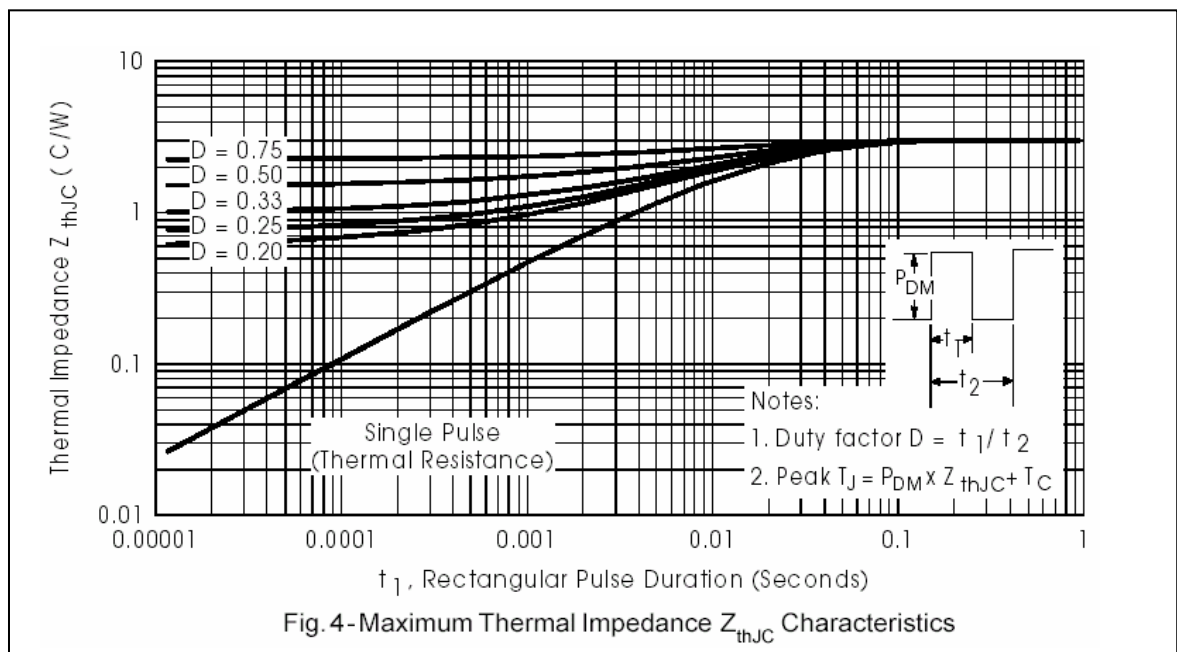
Package Dimensions

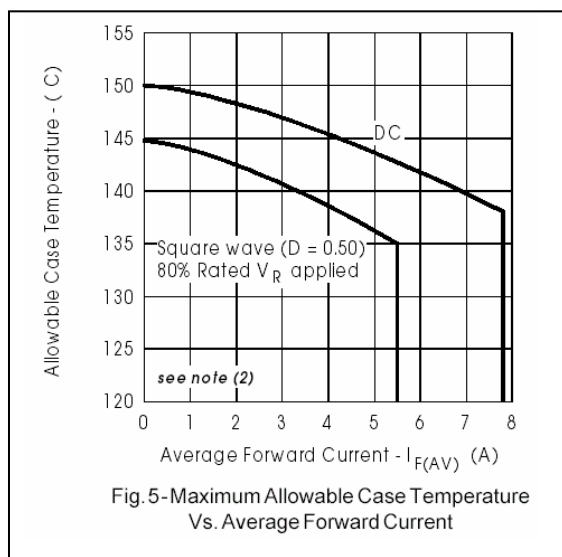
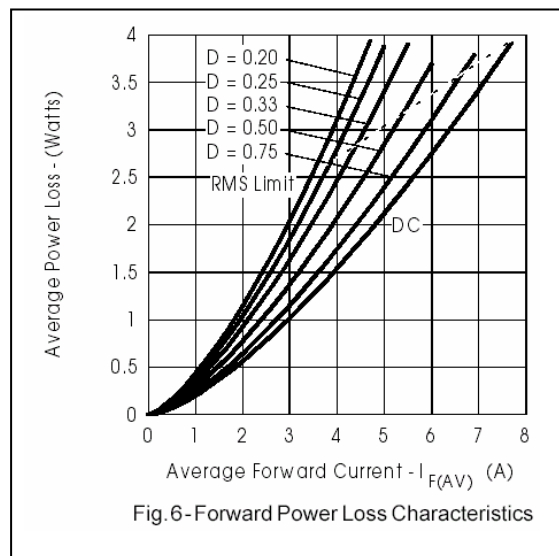
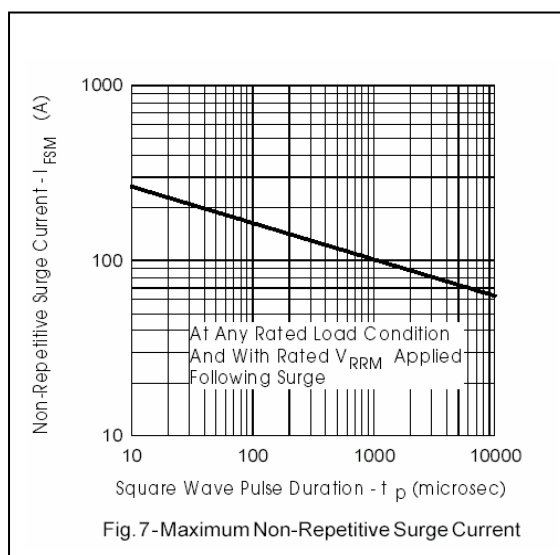


Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	-40~+125	°C
Storage Temperature	T_{stg}	-40~+125	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	3.0	°C/W
Typical Junction Capacitance	C_j	405	pF
Reverse Leakage Current @ $T_j = 25\text{ }^{\circ}\text{C}$ $V_R=40\text{V}$	I_{RM}	0.3	mA
Reverse Leakage Current @ $T_j = 125\text{ }^{\circ}\text{C}$ $V_R=40\text{V}$		40	mA
Forward Voltage Drop @ $I_F = 5.0\text{A}$, $T_j = 25\text{ }^{\circ}\text{C}$	V_{FM}	0.55	V
Forward Voltage Drop @ $I_F = 5.0\text{A}$, $T_j = 125\text{ }^{\circ}\text{C}$		0.44	V
Non-Repetitive Peak Forward Surge Current 5us Single half Sine-wave superimposed on rated load	I_{FSM}	340	A
Non-Repetitive Peak Forward Surge Current 10ms Single half Sine-wave superimposed on rated load		70	
Rectangular waveform	I_F	5.0	A
DC Reverse Voltage	$V_{R(RMS)}$	40	V
Working Peak Reverse Voltage	V_{RWM}	40	V

Characteristics Curve





Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-58957671-4 FAX : 86-21-38950165